

GENERAL DESCRIPTION

Passivated guaranteed commutation triacs in a full pack, plastic envelope intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

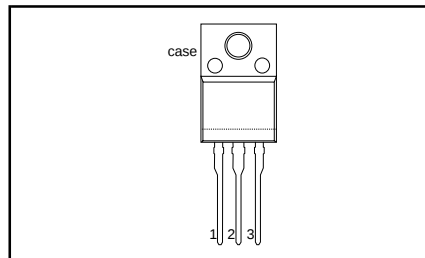
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages BTA212X- BTA212X- BTA212X-	600D 600E 600F 600	- 800E 800F 800	V
$I_{\text{T(RMS)}}$	RMS on-state current	12	12	A
I_{TSM}	Non-repetitive peak on-state current	95	95	A

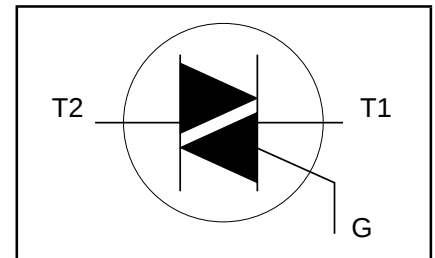
PINNING - TO220F

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-600 600¹	-800 800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{hs}} \leq 56^\circ\text{C}$	-	12		A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_{\text{j}} = 25^\circ\text{C}$ prior to surge $t = 20\text{ ms}$	-	95		A
		$t = 16.7\text{ ms}$	-	105		A
		$t = 10\text{ ms}$	-	45		A ² s
I^2t	I^2t for fusing			100		A/μs
di_{T}/dt	Repetitive rate of rise of on-state current after triggering	$I_{\text{TM}} = 20\text{ A}; I_{\text{G}} = 0.2\text{ A}; di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$				
I_{GM}	Peak gate current		-	2		A
V_{GM}	Peak gate voltage		-	5		V
P_{GM}	Peak gate power		-	5		W
$P_{\text{G(AV)}}$	Average gate power	over any 20 ms period	-	0.5		W
T_{stg}	Storage temperature		-40	150		°C
T_{j}	Operating junction temperature		-	125		°C

1 Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/μs.

ISOLATION LIMITING VALUE & CHARACTERISTIC

$T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	$f = 50\text{-}60\text{ Hz}$; sinusoidal waveform; $R.H. \leq 65\%$; clean and dustfree	-	-	2500	V
C_{isol}	Capacitance from T2 to external heatsink	$f = 1\text{ MHz}$	-	10	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Thermal resistance junction to heatsink	full or half cycle with heatsink compound	-	-	4.0	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	without heatsink compound in free air	-	55	5.5	K/W

STATIC CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

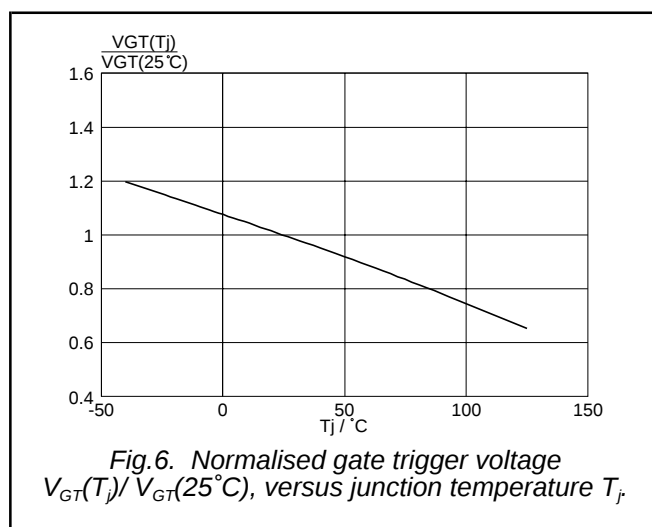
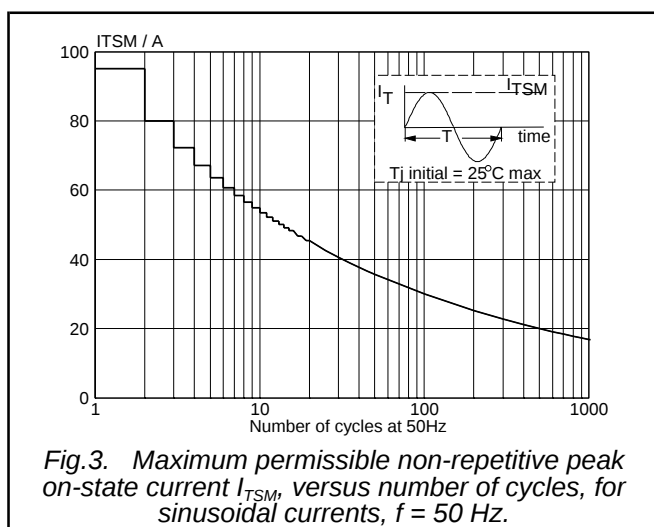
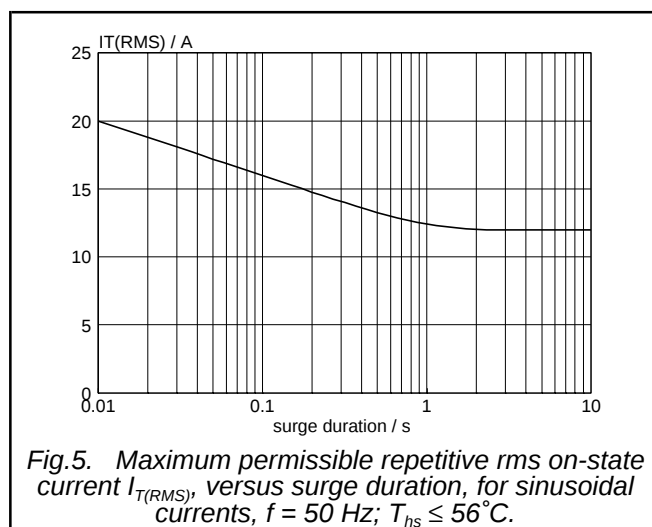
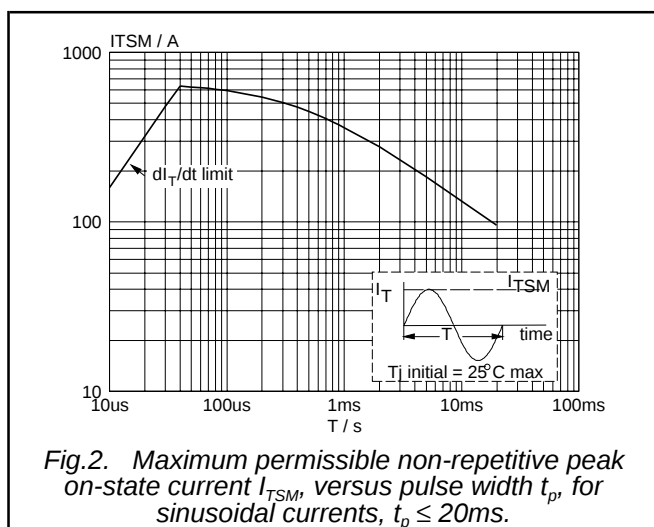
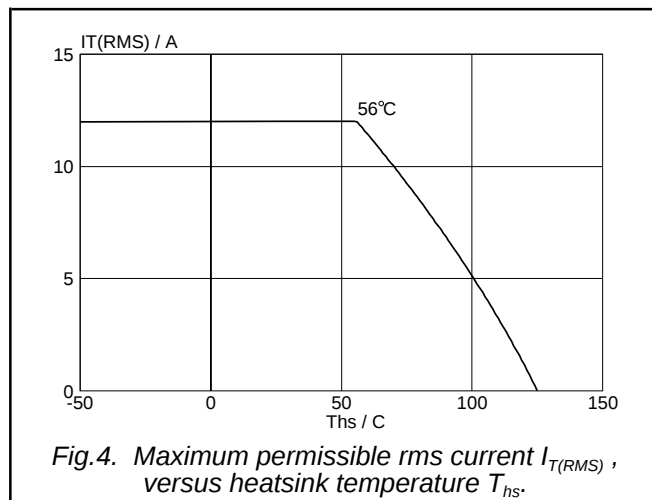
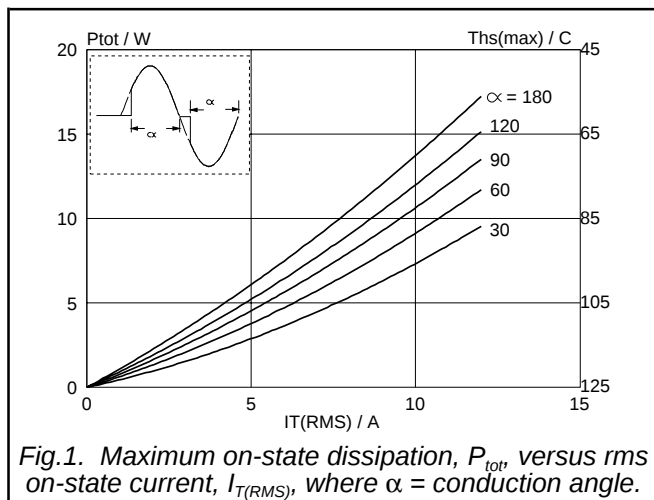
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.			UNIT
		BTA212X-		...D	...D	...E	...F	
I_{GT}	Gate trigger current ²	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$	-	1.0	5	10	25	mA
		T2+ G+	-	2.2	5	10	25	mA
		T2- G-	-	3.3	5	10	25	mA
I_L	Latching current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$	-	6	15	25	30	mA
		T2+ G+	-	6	25	30	40	mA
		T2- G-	-	9	25	30	40	mA
I_H	Holding current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$	-	3.8	15	25	30	mA
V_T	On-state voltage	$I_T = 17\text{ A}$	-	1.3	1.6			V
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$	-	0.7	1.5			V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ }^{\circ}\text{C}$	0.25	0.4	-			V
I_D	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125\text{ }^{\circ}\text{C}$	-	0.1	0.5			mA

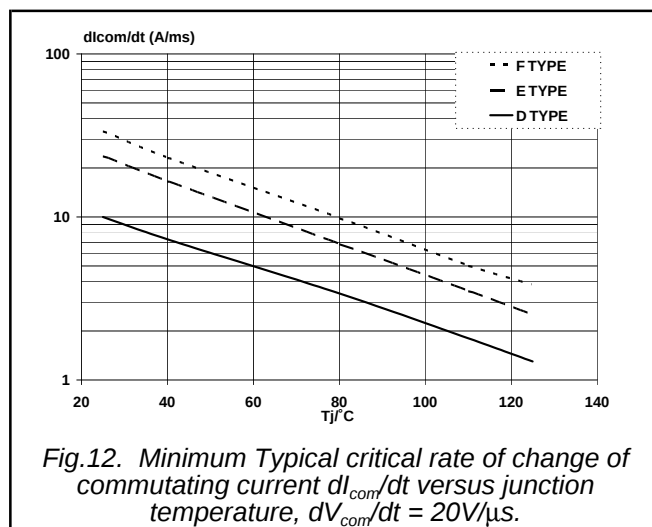
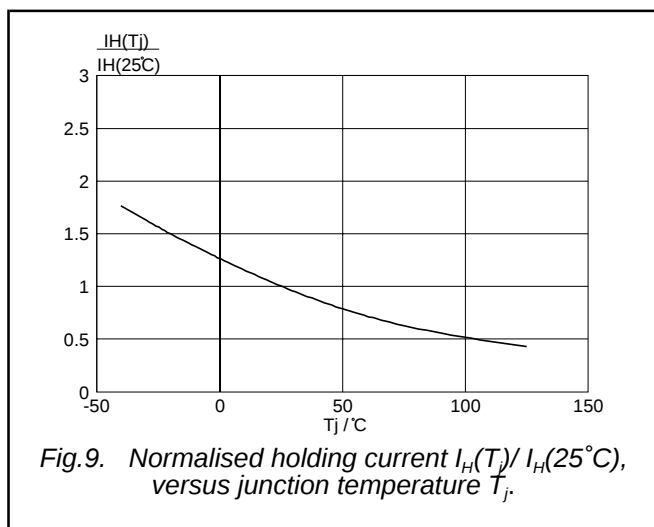
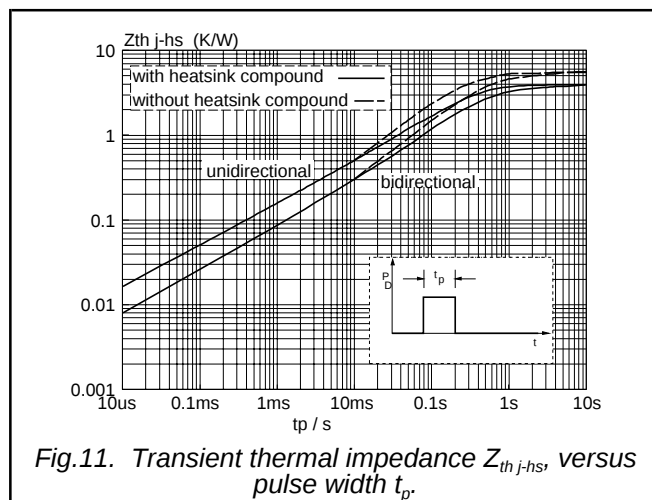
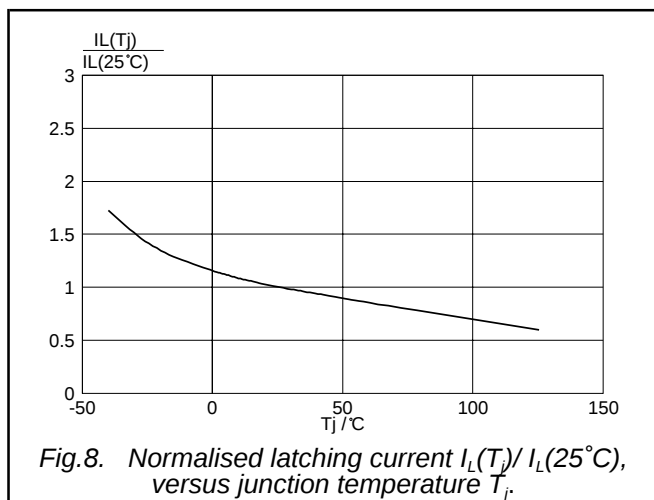
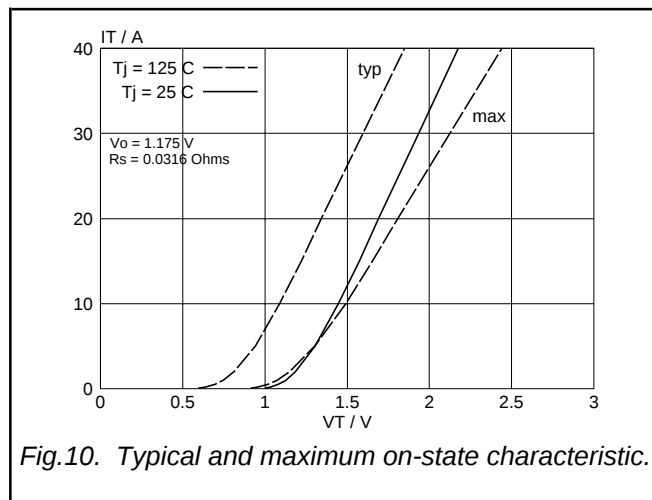
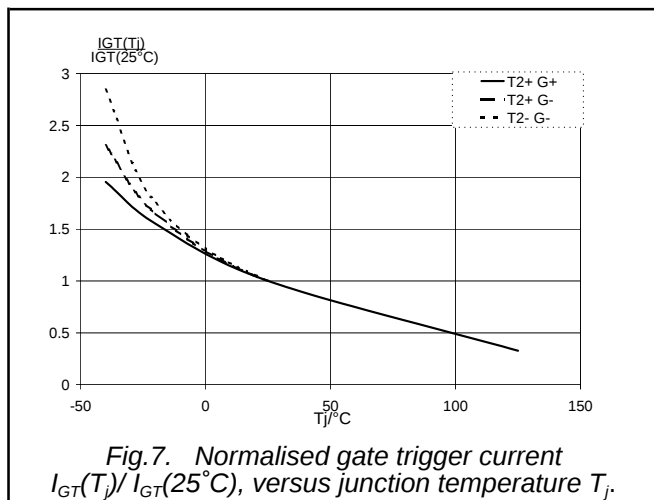
² Device does not trigger in the T2-, G+ quadrant.

DYNAMIC CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.			TYP.	MAX.	UNIT
		BTA212X-	...D	...E	...F	...D		
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}$; $T_j = 110\text{ }^{\circ}\text{C}$; exponential waveform; gate open circuit	20	60	70	30	-	V/ μs
dI_{com}/dt	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}$; $T_j = 110\text{ }^{\circ}\text{C}$; $I_{T(RMS)} = 12\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; gate open circuit	1.8	3.5	5	3	-	A/ms
dI_{com}/dt	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}$; $T_j = 110\text{ }^{\circ}\text{C}$; $I_{T(RMS)} = 12\text{ A}$; $dV_{com}/dt = 0.1\text{ V}/\mu\text{s}$; gate open circuit	5	16	19	100	-	A/ms
			...D, E, F					
t_{gt}	Gate controlled turn-on time	$I_{TM} = 12\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$	-	-	-	2	-	μs





MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

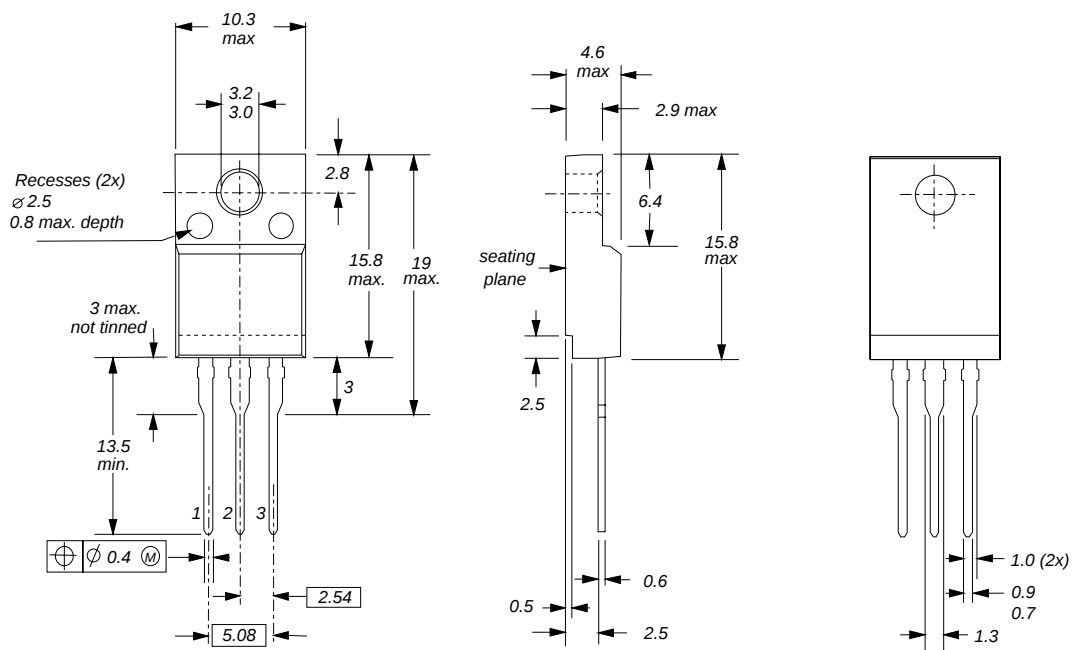


Fig.13. TO220F; The seating plane is electrically isolated from all terminals.

Notes

1. Refer to mounting instructions for F-pack envelopes.
2. Epoxy meets UL94 V0 at 1/8".